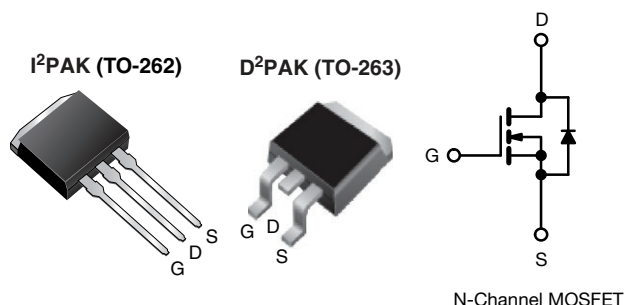


Power MOSFET



N-Channel MOSFET

FEATURES

- Surface-mount
- Available in tape and reel
- Dynamic dv/dt rating
- Repetitive avalanche rated
- Fast switching
- Ease of paralleling
- Simple drive requirements
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS*
Available
HALOGEN
FREE
Available

Note

* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details

DESCRIPTION

Third generation power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The D²PAK (TO-263) is a surface-mount power package capable of accommodating die size up to HEX-4. It provides the highest power capability and the lowest possible on-resistance in any existing surface-mount package. The D²PAK (TO-263) is suitable for high current applications because of its low internal connection resistance and can dissipate up to 2.0 W in a typical surface-mount application.

PRODUCT SUMMARY	
V _{DS} (V)	400
R _{DS(on)} (Ω)	V _{GS} = 10 V 1.8
Q _g max. (nC)	20
Q _{gs} (nC)	3.3
Q _{gd} (nC)	11
Configuration	Single

ORDERING INFORMATION				
Package	D²PAK (TO-263)	D²PAK (TO-263)	D²PAK (TO-263)	I²PAK (TO-262)
Lead (Pb)-free and halogen-free	SiHF720S-GE3	SiHF720STRR-GE3 ^a	SiHF720STRL-GE3 ^a	SiHF720L-GE3
Lead (Pb)-free	IRF720SPbF	IRF720STRRPbF ^a	-	IRF720LPbF

Note

a. See device orientation

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V _{DS}	400	V
Gate-source voltage		V _{GS}	± 20	
Continuous drain current	V _{GS} at 10 V	I _D	3.3	A
			2.1	
Pulsed drain current ^a		I _{DM}	13	W/°C
Linear derating factor			0.40	
Linear derating factor (PCB mount) ^e			0.025	
Single pulse avalanche energy ^b		E _{AS}	190	mJ
Avalanche current ^a		I _{AR}	3.3	A
Repetitive avalanche energy ^a		E _{AR}	5.0	mJ
Maximum power dissipation	T _C = 25 °C	P _D	50	W
Maximum power dissipation (PCB mount) ^e	T _A = 25 °C		3.1	
Peak diode recovery dv/dt ^c		dv/dt	4.0	V/ns
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +150	°C
Soldering recommendations (peak temperature) ^d	For 10 s		300	

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
- V_{DD} = 50 V, starting T_J = 25 °C, L = 30 mH, R_g = 25 Ω, I_{AS} = 3.3 A (see fig. 12)
- I_{SD} ≤ 3.3 A, di/dt ≤ 65 A/μs, V_{DD} ≤ V_{DS}, T_J ≤ 150 °C
- 1.6 mm from case
- When mounted on 1" square PCB (FR-4 or G-10 material)

**THERMAL RESISTANCE RATINGS**

PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum junction-to-ambient	R_{thJA}	-	62	°C/W
Maximum junction-to-ambient (PCB mount) ^a	R_{thJA}	-	40	
Maximum junction-to-case (Drain)	R_{thJC}	-	2.5	

Note

a. When mounted on 1" square PCB (FR-4 or G-10 material)

SPECIFICATIONS ($T_J = 25\text{ °C}$, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V _{DS}	V _{GS} = 0, I _D = 250 μA		400	-	-	V
V _{DS} temperature coefficient	ΔV _{DS} /T _J	Reference to 25 °C, I _D = 1 mA		-	0.51	-	V/°C
Gate-source threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA		2.0	-	4.0	V
Gate-source leakage	I _{GSS}	V _{GS} = ± 20 V		-	-	± 100	nA
Zero gate voltage drain current	I _{DSS}	V _{DS} = 400 V, V _{GS} = 0 V		-	-	25	μA
		V _{DS} = 320 V, V _{GS} = 0 V, T _J = 125 °C		-	-	250	
Drain-source on-state resistance	R _{DS(on)}	V _{GS} = 10 V	I _D = 2.0 A ^b	-	-	1.8	Ω
Forward transconductance	g _{fs}	V _{DS} = 50 V, I _D = 2.0 A ^b		1.7	-	-	S
Dynamic							
Input capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1.0 MHz, see fig. 5		-	410	-	pF
Output capacitance	C _{oss}			-	120	-	
Reverse transfer capacitance	C _{rss}			-	47	-	
Total gate charge	Q _g	V _{GS} = 10 V	I _D = 3.3 A, V _{DS} = 320 V, see fig. 6 and 13 ^b	-	-	20	nC
Gate-source charge	Q _{gs}			-	-	3.3	
Gate-drain charge	Q _{gd}			-	-	11	
Turn-on delay time	t _{d(on)}	V _{DD} = 200 V, I _D = 3.3 A, R _g = 18 Ω, R _D = 56 Ω, see fig. 10 ^b		-	10	-	ns
Rise time	t _r			-	14	-	
Turn-off delay time	t _{d(off)}			-	30	-	
Fall time	t _f			-	13	-	
Gate input resistance	R _g	f = 1 MHz, open drain		1.2	-	7.3	Ω
Internal drain inductance	L _D	Between lead, 6 mm (0.25") from package and center of die contact		-	4.5	-	nH
Internal source inductance	L _S			-	7.5	-	
Drain-Source Body Diode Characteristics							
Continuous source-drain diode current	I _S	MOSFET symbol showing the integral reverse p - n junction diode		-	-	3.3	A
Pulsed diode forward current ^a	I _{SM}			-	-	13	
Body diode voltage	V _{SD}	T _J = 25 °C, I _S = 3.3 A, V _{GS} = 0 V ^b		-	-	1.6	V
Body diode reverse recovery time	t _{rr}	T _J = 25 °C, I _F = 3.3 A, di/dt = 100 A/μs ^b		-	270	600	ns
Body diode reverse recovery charge	Q _{rr}			-	1.4	3.0	μC
Forward turn-on time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L _S and L _D)					

Notes

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
b. Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

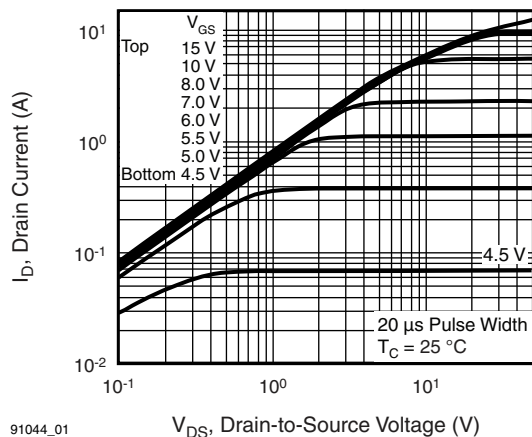


Fig. 1 - Typical Output Characteristics, $T_C = 25$ °C

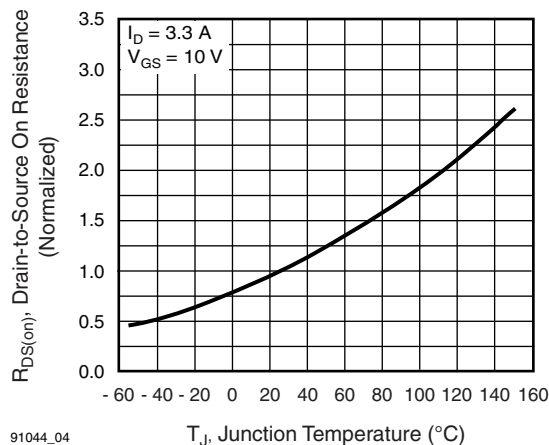


Fig. 4 - Normalized On-Resistance vs. Temperature

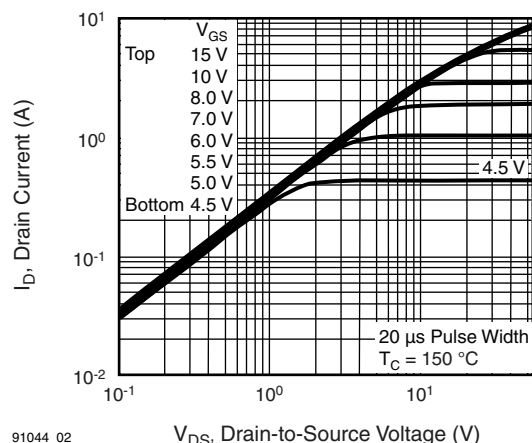


Fig. 2 - Typical Output Characteristics, $T_C = 150$ °C

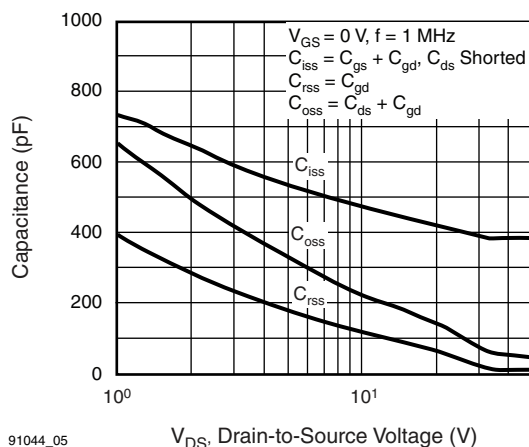


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

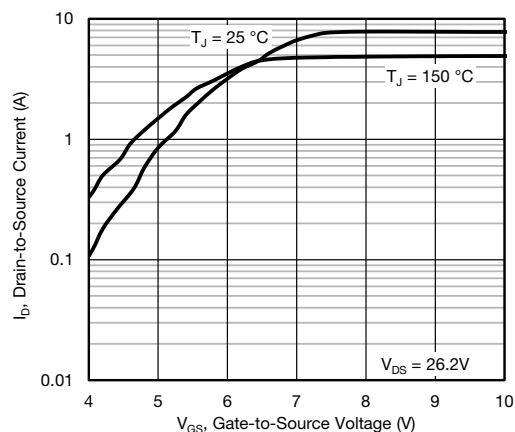


Fig. 3 - Typical Transfer Characteristics

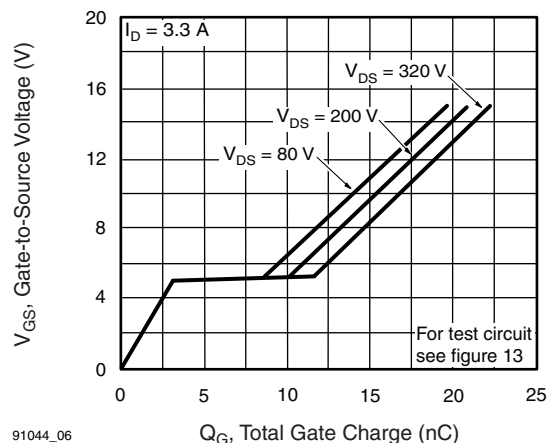


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

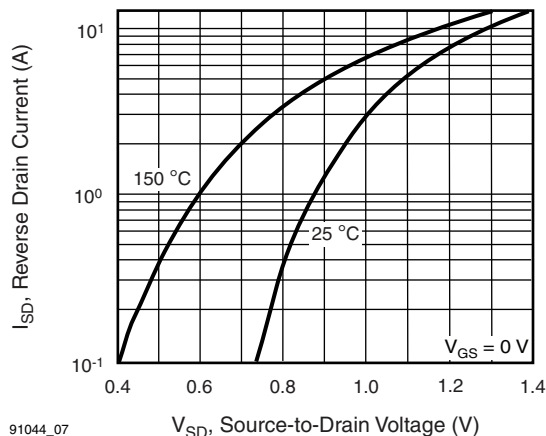


Fig. 7 - Typical Source-Drain Diode Forward Voltage

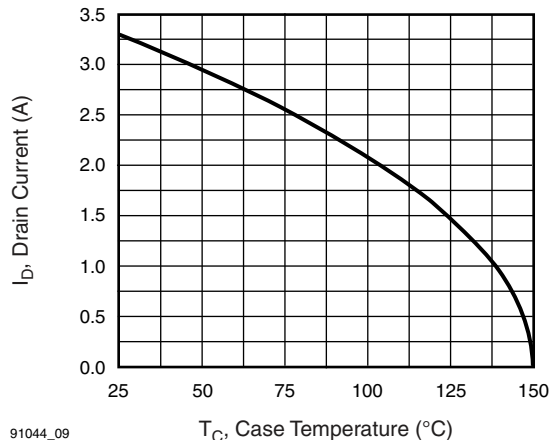


Fig. 9 - Maximum Drain Current vs. Case Temperature

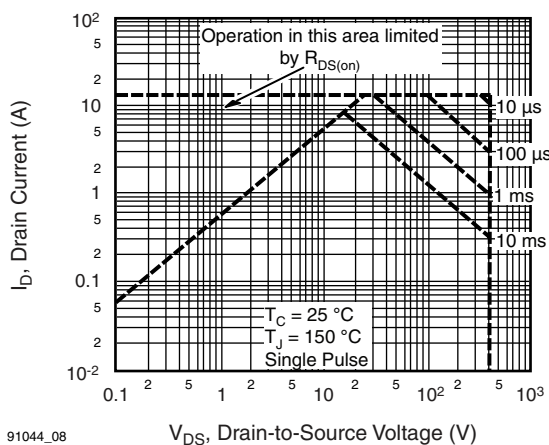


Fig. 8 - Maximum Safe Operating Area

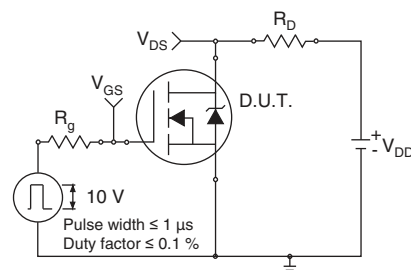


Fig. 10a - Switching Time Test Circuit

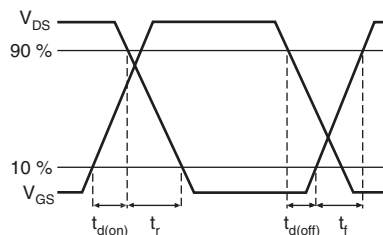


Fig. 10b - Switching Time Waveforms

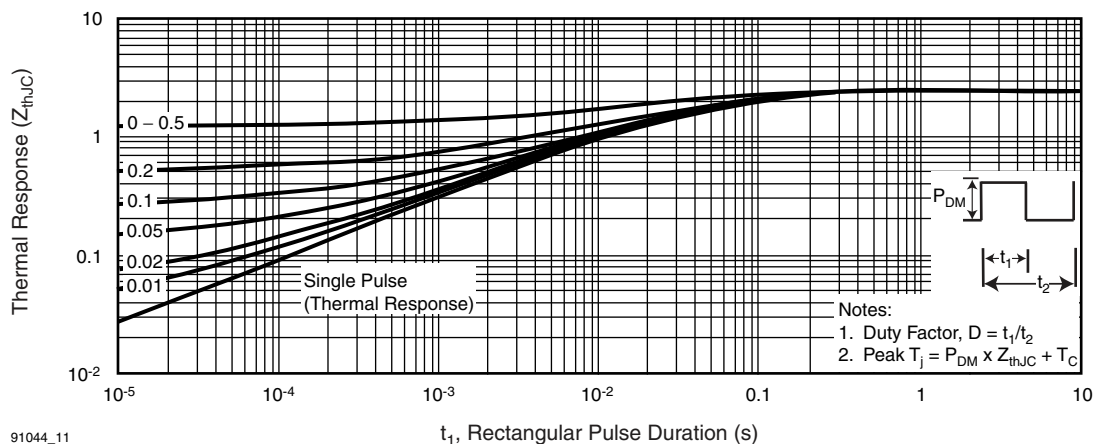


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

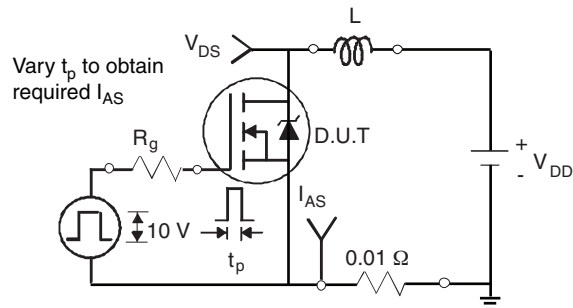


Fig. 12a - Unclamped Inductive Test Circuit

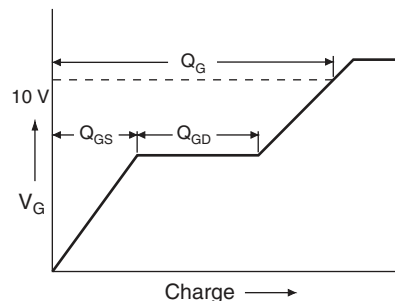


Fig. 13a - Basic Gate Charge Waveform

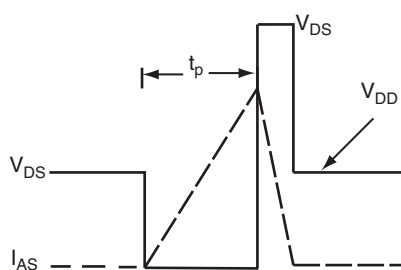


Fig. 12b - Unclamped Inductive Waveforms

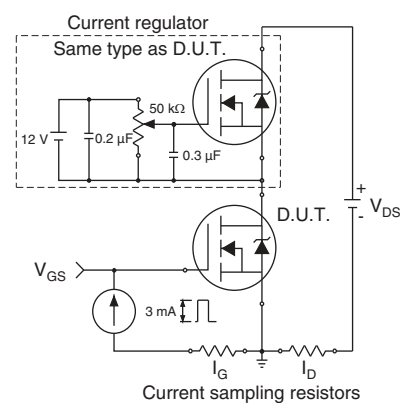


Fig. 13b - Gate Charge Test Circuit

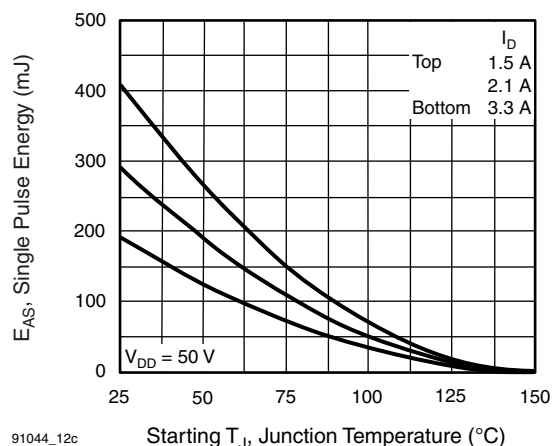
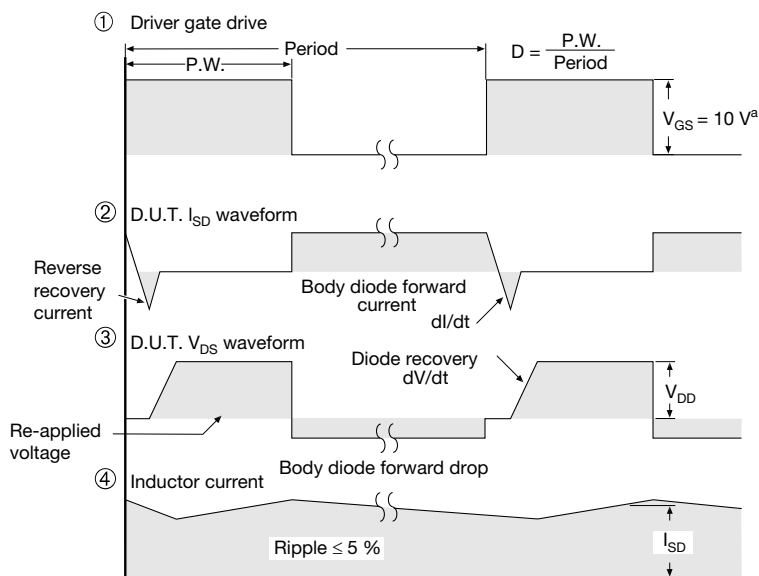
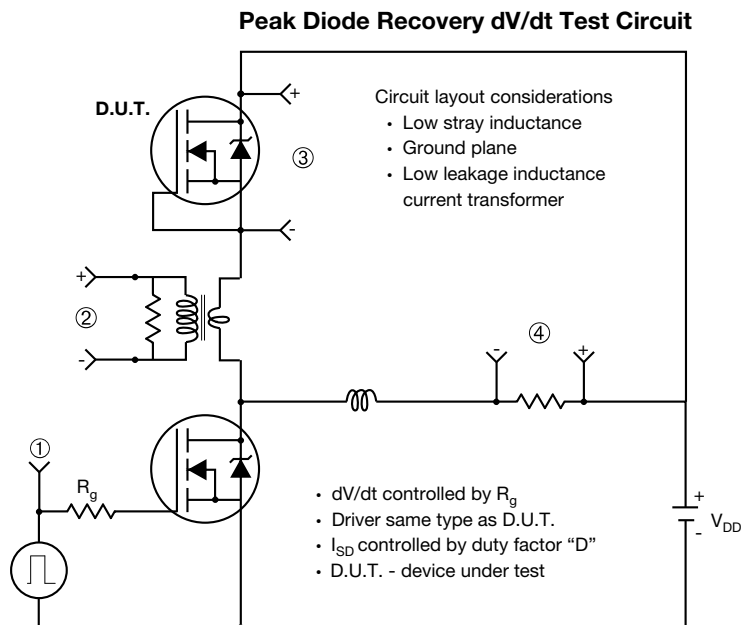


Fig. 12c - Maximum Avalanche Energy vs. Drain Current



Note

a. $V_{GS} = 5\text{ V}$ for logic level devices

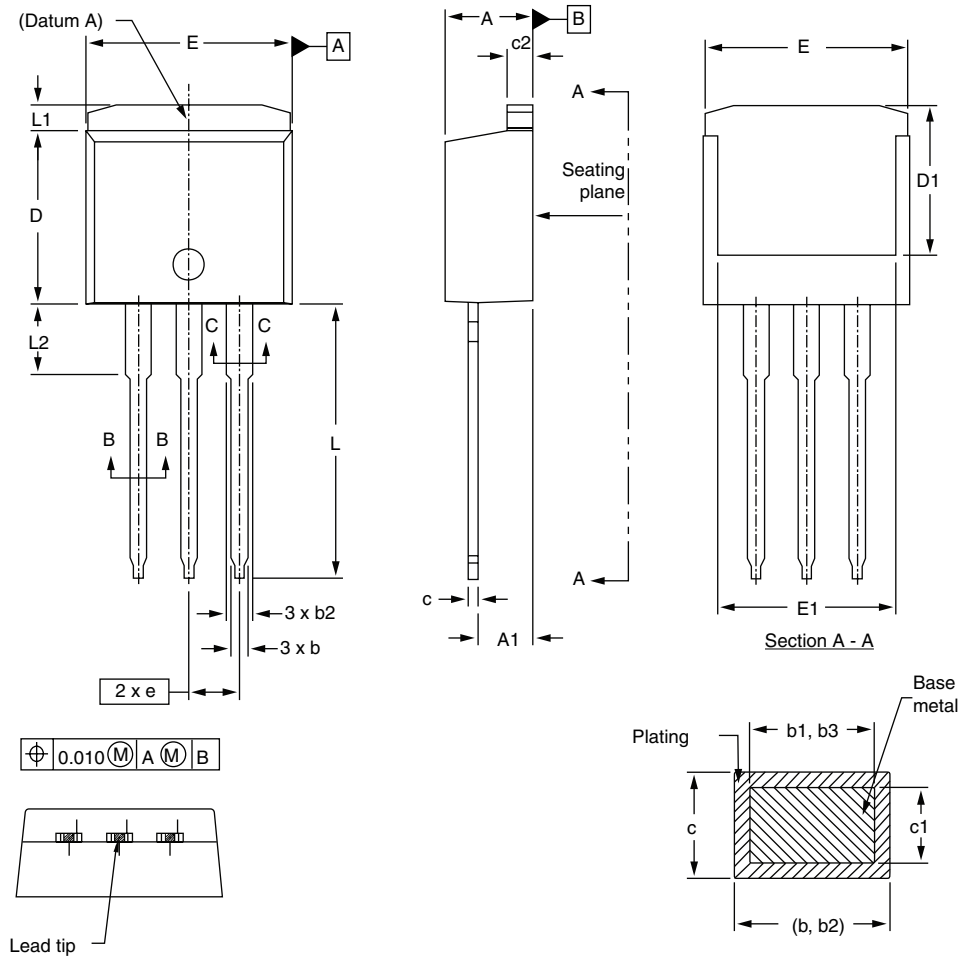
Fig. 14 - For N-Channel

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?91044.

	MILLIMETERS		INCHES	
DIM.	MIN.	MAX.	MIN.	MAX.
D1	6.86	-	0.270	-
E	9.65	10.67	0.380	0.420
E1	6.22	-	0.245	-
e	2.54 BSC		0.100 BSC	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	-	1.65	-	0.066
L2	-	1.78	-	0.070
L3	0.25 BSC		0.010 BSC	
L4	4.78	5.28	0.188	0.208

—

I²PAK (TO-262) (HIGH VOLTAGE)



	MILLIMETERS		INCHES	
DIM.	MIN.	MAX.	MIN.	MAX.
A	4.06	4.83	0.160	0.190
A1	2.03	3.02	0.080	0.119
b	0.51	0.99	0.020	0.039
b1	0.51	0.89	0.020	0.035
b2	1.14	1.78	0.045	0.070
b3	1.14	1.73	0.045	0.068
c	0.38	0.74	0.015	0.029
c1	0.38	0.58	0.015	0.023
c2	1.14	1.65	0.045	0.065

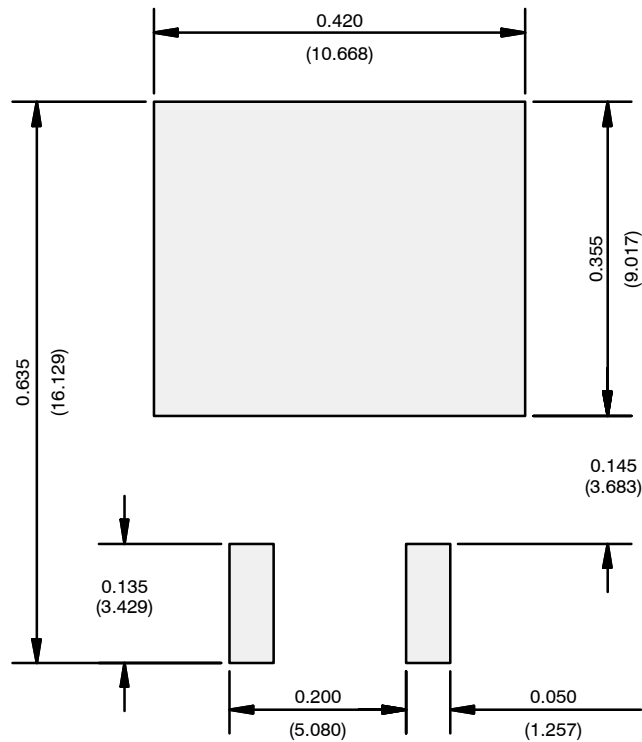
	MILLIMETERS		INCHES	
DIM.	MIN.	MAX.	MIN.	MAX.
D	8.38	9.65	0.330	0.380
D1	6.86	-	0.270	-
E	9.65	10.67	0.380	0.420
E1	6.22	-	0.245	-
e	2.54 BSC		0.100 BSC	
L	13.46	14.10	0.530	0.555
L1	-	1.65	-	0.065
L2	3.56	3.71	0.140	0.146

ECN: S-82442-Rev. A, 27-Oct-08
DWG: 5977

Notes

1. Dimensioning and tolerancing per ASME Y14.5M-1994.
2. Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm per side. These dimensions are measured at the outmost extremes of the plastic body.
3. Thermal pad contour optional within dimension E, L1, D1, and E1.
4. Dimension b1 and c1 apply to base metal only.

RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads
Dimensions in Inches/(mm)

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